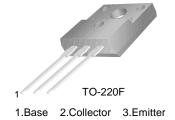


### **KSB1015**

### **Low Frequency Power Amplifier**

- Low Collector Emitter Saturation Voltage
- Complement to KSD1406



## **PNP Epitaxial Silicon Transistor**

## Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	- 60	V
$V_{CEO}$	Collector-Emitter Voltage	- 60	V
V <sub>EBO</sub>	Emitter-Base Voltage	- 7	V
I <sub>C</sub>	Collector Current(DC)	- 3	Α
I <sub>B</sub>	Base Current	- 0.5	Α
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	25	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 55 ~ 150	°C

### Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_C = -50 \text{mA}, I_B = 0$	- 60			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = -60V, I_{E} = 0$			- 100	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = -7V, I_{C} = 0$			- 100	μΑ
h <sub>FE1</sub>	DC Current Gain	$V_{CE} = -5V, I_{C} = -0.5A$	60		200	
h <sub>FE2</sub>		$V_{CE} = -5V, I_{C} = -3A$	20			
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	$I_C = -3A$ , $I_B = -0.3A$		- 0.5	- 1	V
V <sub>BE</sub> (on)	Base-Emitter ON Voltage	$V_{CE} = -5V, I_{C} = -0.5A$		- 0.7	- 1	V
f <sub>T</sub>	Current Gain Bandwidth Product	$V_{CE} = -5V, I_{C} = -0.5A$		9		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = - 10V, f = 1MHz		150		pF
t <sub>ON</sub>	Turn ON Time	$V_{CC} = -30V, I_{C} = -1A$		0.4		μs
t <sub>STG</sub>	Storage Time	$I_{B1} = -I_{B2} = -0.2A$		1.7		μs
t <sub>F</sub>	Fall Time	$R_L = 30\Omega$		0.5		μs

### **h**<sub>FE</sub> Classification

Classification	0	Y	
h <sub>FE1</sub>	60 ~ 120	100 ~ 200	

# **Typical Characteristics**

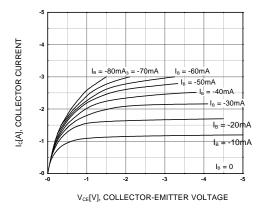


Figure 1. Static Characteristic

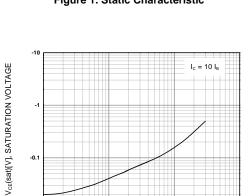


Figure 3. Collector-Emitter Saturation Voltage

I<sub>c</sub>[A], COLLECTOR CURRENT

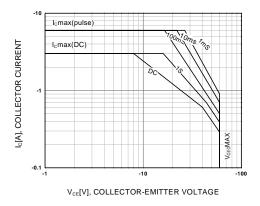


Figure 5. Safe Operating Area

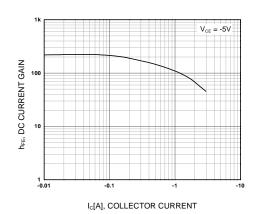


Figure 2. DC current Gain

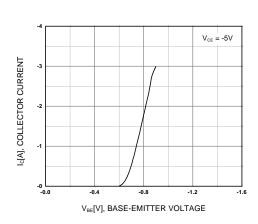


Figure 4. Base-Emitter On Voltage

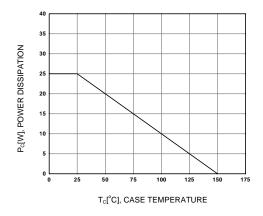


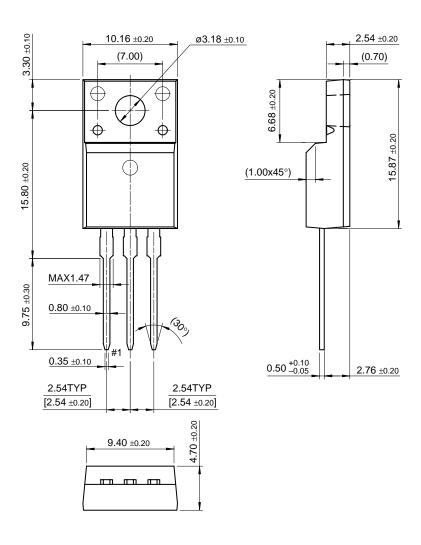
Figure 6. Power Derating

Rev. A, February 2000

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# **Package Demensions**

## TO-220F



Dimensions in Millimeters

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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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